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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	e200z4d, e200z0h
Core Size	32-Bit Dual-Core
Speed	80MHz/120MHz
Connectivity	CANbus, Ethernet, I²C, LINbus, SCI, SPI
Peripherals	DMA, POR, PWM, WDT
Number of I/O	147
Program Memory Size	2MB (2M x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	256K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 27x10b, 5x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	176-LQFP
Supplier Device Package	176-LQFP (24x24)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5645cf0mlu1

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Table 1. MPC5646C family comparison[1] (continued)

Feature	MPC5644B		MPC5644C			MPC5645B		MPC5645C			MPC5646B		MPC5646C		
Package	176 LQFP	208 LQFP	176 LQFP	208 LQFP	256 BGA	176 LQFP	208 LQFP	176 LQFP	208 LQFP	256 BGA	176 LQFP	208 LQFP	176 LQFP	208 LQFP	256 BGA
Ethernet	No		Yes			No		Yes			No		Yes		
I^2C	1														
32 kHz oscillator (SXOSC)	Yes														
GPIO[12]	147	177	147	177	199	147	177	147	177	199	147	177	147	177	199
Debug	JTAG				Nexus 3+	JTAG				Nexus 3+	JTAG				Nexus 3+
Cryptographic Services Engine (CSE)	Optional														

NOTES:
1 Feature set dependent on selected peripheral multiplexing; table shows example.
2 Based on 125 °C ambient operating temperature and subject to full device characterisation.
3 The e200z0h can run at speeds up to 80 MHz. However, if system frequency is >80 MHz (e.g., e200z4d running at 120 MHz) the e200z0h needs to run at 1/2 system frequency. There is a configurable e200z0 system clock divider for this purpose.
4 DMAMUX also included that allows for software selection of 32 out of a possible 57 sources.
5 Not shared with 12-bit ADC, but possibly shared with other alternate functions.
6 There are 23 dedicated ANS plus 4 dedicated ANX channels on LQPF176. For higher pin count packages, there are 29 dedicated ANS plus 4 dedicated ANX channels.
7 16x precision channels (ANP) and 3x standard (ANS).
8 Not shared with 10-bit ADC, but possibly shared with other alternate functions.
9 As a minimum, all timer channels can function as PWM or Input Capture and Output Control. Refer to the eMIOS section of the device reference manual for information on the channel configuration and functions.
10 CAN Sampler also included that allows ID of CAN message to be captured when in low power mode.
11 STCU controls MBIST activation and reporting.
12 Estimated I/O count for proposed packages based on multiplexing with peripherals.

F = Fast[1, 2]

I = Input only with analog feature[1]

A = Analog

3.2 System pins

The system pins are listed in Table 3.

Table 3. System pin descriptions

Port pin	Function	I/O direction	Pad type	RESET config.	Pin number		
					176 LQFP	208 LQFP	256 MAPBGA
$\overline{\text{RESET}}$	Bidirectional reset with Schmitt-Trigger characteristics and noise filter.	I/O	M	Input, weak pull-up only after PHASE2	29	29	K1
EXTAL	Analog input of the oscillator amplifier circuit. Needs to be grounded if oscillator bypass mode is used.	I	A[1]	—	58	74	T8
XTAL	Analog output of the oscillator amplifier circuit, when the oscillator is not in bypass mode. Analog input for the clock generator when the oscillator is in bypass mode.	I/O	A[1]	—	56	72	T7

NOTES:
1 For analog pads, it is not recommended to enable IBE if APC is enabled to avoid extra current in middle range voltage.

3.3 Functional ports

The functional port pins are listed in Table 4.

Table 4. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET config.	Pin number		
								176 LQFP	208 LQFP	256 MAPBGA
PD[8]	PCR[56]	AF0 AF1 AF2 AF3 — —	GPI[56] — — — ADC0_P[12] ADC1_P[12]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	87	103	P14
PD[9]	PCR[57]	AF0 AF1 AF2 AF3 — —	GPI[57] — — — ADC0_P[13] ADC1_P[13]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	94	114	N16
PD[10]	PCR[58]	AF0 AF1 AF2 AF3 — —	GPI[58] — — — ADC0_P[14] ADC1_P[14]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	95	115	M14
PD[11]	PCR[59]	AF0 AF1 AF2 AF3 — —	GPI[59] — — — ADC0_P[15] ADC1_P[15]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	96	116	M15
PD[12]	PCR[60]	AF0 AF1 AF2 AF3 —	GPIO[60] CS5_0 E0UC[24] — ADC0_S[4]	SIUL DSPI_0 eMIOS_0 — ADC_0	I/O O I/O — I	S	Tristate	100	120	L13
PD[13]	PCR[61]	AF0 AF1 AF2 AF3 —	GPIO[61] CS0_1 E0UC[25] — ADC0_S[5]	SIUL DSPI_1 eMIOS_0 — ADC_0	I/O I/O I/O — I	S	Tristate	102	124	K14
PD[14]	PCR[62]	AF0 AF1 AF2 AF3 ALT4 —	GPIO[62] CS1_1 E0UC[26] — FR_DBG[0] ADC0_S[6]	SIUL DSPI_1 eMIOS_0 — Flexray ADC_0	I/O O I/O — O I	S	Tristate	104	126	K13

Table 4. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET config.	Pin number		
								176 LQFP	208 LQFP	256 MAPBGA
PI[7]	PCR[135]	AF0 AF1 AF2 AF3 ALT4	GPIO[135] E1UC[31] CS1_4 CS1_5 CS1_6	SIUL eMIOS_1 DSPI_4 DSPI_5 DSPI_6	I/O I/O O O O	S	Tristate	12	12	E2
PI[8]	PCR[136]	AF0 AF1 AF2 AF3 —	GPIO[136] — — — ADC0_S[16]	SIUL — — — ADC_0	I/O — — — I	S	Tristate	108	130	J14
PI[9]	PCR[137]	AF0 AF1 AF2 AF3 —	GPIO[137] — — — ADC0_S[17]	SIUL — — — ADC_0	I/O — — — I	S	Tristate	—	131	J15
PI[10]	PCR[138]	AF0 AF1 AF2 AF3 —	GPIO[138] — — — ADC0_S[18]	SIUL — — — ADC_0	I/O — — — I	S	Tristate	—	134	J16
PI[11]	PCR[139]	AF0 AF1 AF2 AF3 — —	GPIO[139] — — — ADC0_S[19] SIN_3	SIUL — — — ADC_0 DSPI_3	I/O — — — I I	S	Tristate	111	135	H16
PI[12]	PCR[140]	AF0 AF1 AF2 AF3 —	GPIO[140] CS0_3 CS0_2 — ADC0_S[20]	SIUL DSPI_3 DSPI_2 — ADC_0	I/O I/O I/O — I	S	Tristate	112	136	G15
PI[13]	PCR[141]	AF0 AF1 AF2 AF3 —	GPIO[141] CS1_3 CS1_2 — ADC0_S[21]	SIUL DSPI_3 DSPI_2 — ADC_0	I/O O O — I	S	Tristate	113	137	G14
PI[14]	PCR[142]	AF0 AF1 AF2 AF3 — —	GPIO[142] — — — ADC0_S[22] SIN_4	SIUL — — — ADC_0 DSPI_4	I/O — — — I I	S	Tristate	76	92	T12

Table 20. I/O consumption (continued)

Symbol		C	Parameter	Conditions[1,2]	Value[3]			Unit
					Min	Typ	Max	
I_{AVGSEG}	SR	D	Sum of all the static I/O current within a supply segment	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	70	mA
				V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	65[4]	

NOTES:
1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.
2. V_{DD} as mentioned in the table is $V_{DD\_HV\_A}$/$V_{DD\_HV\_B}$.
3. All values need to be confirmed during device validation.
4. Stated maximum values represent peak consumption that lasts only a few ns during I/O transition.

4.7 RESET electrical characteristics

The device implements a dedicated bidirectional $\overline{\text{RESET}}$ pin.

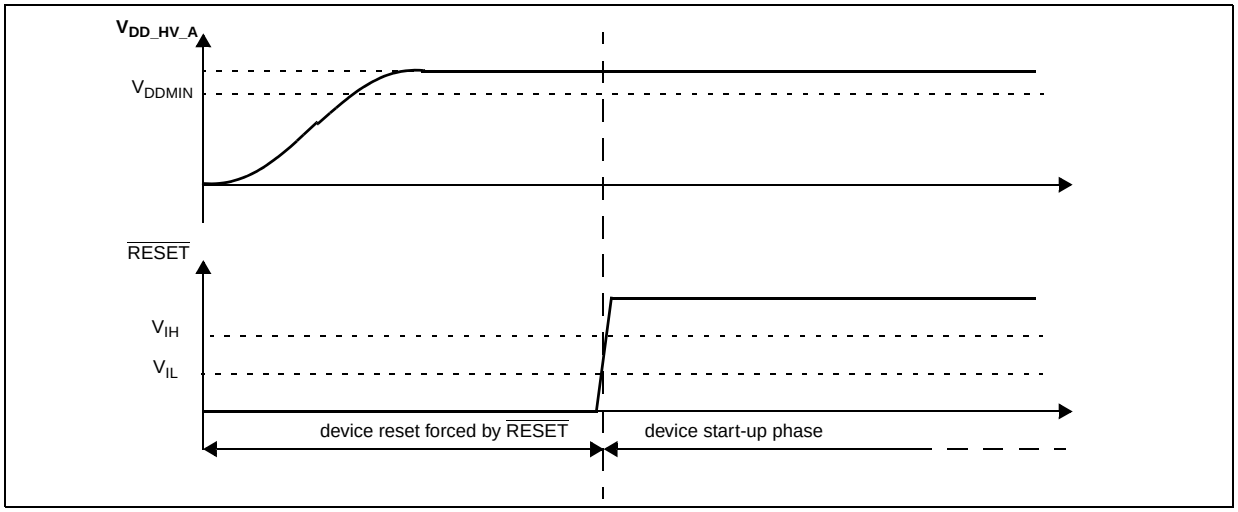


Figure 6. Start-up reset requirements

3 Data based on characterization results, not tested in production.

4 f_{CPU} 120 MHz + 2% can be achieved over full temperature 125 °C ambient, 150 °C junction temperature.

4.10.3 Flash memory start-up/switch-off timings

Table 30. Start-up time/Switch-off time

Symbol		C	Parameter		Conditions[1]	Value			Unit
						Min	Typ	Max	
$T_{FLARSTEXIT}$	CC	D	Delay for flash memory module to exit reset mode	Code flash memory	—	—	—	125	µs
				Data flash memory		—	—		
$T_{FLALPEXIT}$	CC	T	Delay for flash memory module to exit low-power mode	Code flash memory	—	—	—	0.5	
$T_{FLAPDEXIT}$	CC	T	Delay for flash memory module to exit power-down mode	Code flash memory	—	—	—	30	
				Data flash memory		—	—		
$T_{FLALPENTRY}$	CC	T	Delay for flash memory module to enter low-power mode	Code flash memory	—	—	—	0.5	

NOTES:
1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.

4.11 Electromagnetic compatibility (EMC) characteristics

Susceptibility tests are performed on a sample basis during product characterization.

4.11.1 Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user apply EMC software optimization and pre-qualification tests in relation with the EMC level requested for the application.

- Software recommendations – The software flowchart must include the management of runaway conditions such as:
  - Corrupted program counter
  - Unexpected reset
  - Critical data corruption (control registers)
- Pre-qualification trials – Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the reset pin or the oscillator pins for 1 second.

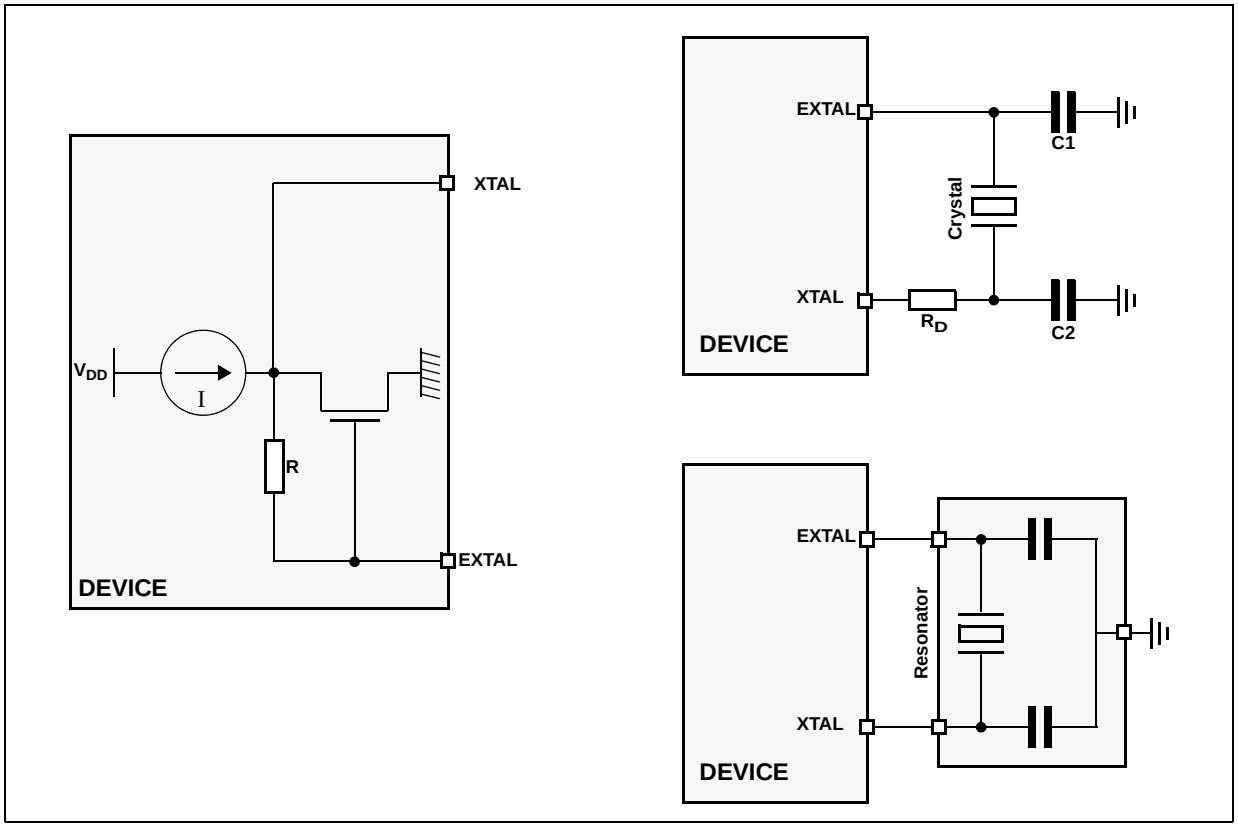


Figure 10. Crystal oscillator and resonator connection scheme

NOTE

XTAL/EXTAL must not be directly used to drive external circuits.

Table 34. Crystal description

Nominal frequency (MHz)	NDK crystal reference	Crystal equivalent series resistance ESR Ω	Crystal motional capacitance (C_m) fF	Crystal motional inductance (L_m) mH	Load on xtalin/xtalout C1 = C2 (pF)[1]	Shunt capacitance between xtalout and xtalin C0[2] (pF)
4	NX8045GB	300	2.68	591.0	21	2.93
8	NX5032GA	300	2.46	160.7	17	3.01
10		150	2.93	86.6	15	2.91
12		120	3.11	56.5	15	2.93
16		120	3.90	25.3	10	3.00
40	NX5032GA	50	6.18	2.56	8	3.49

NOTES:
1 The values specified for C1 and C2 are the same as used in simulations. It should be ensured that the testing includes all the parasitics (from the board, probe, crystal, etc.) as the AC / transient behavior depends upon them.
2 The value of C0 specified here includes 2 pF additional capacitance for parasitics (to be seen with bond-pads, package, etc.).

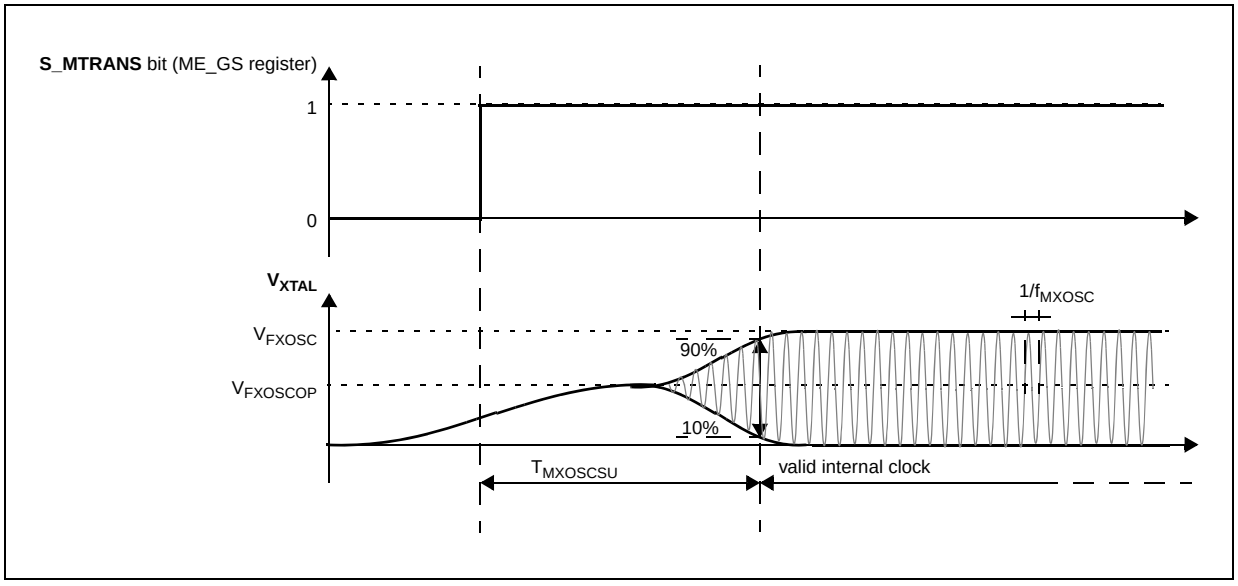


Figure 11. Fast external crystal oscillator (4 to 40 MHz) electrical characteristics

Table 35. Fast external crystal oscillator (4 to 40 MHz) electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value[2]			Unit
					Min	Typ	Max	
f_{FXOSC}	SR	—	Fast external crystal oscillator frequency	—	4.0	—	40.0	MHz
g_{mFXOSC}	CC	C	Fast external crystal oscillator transconductance	V_{DD} = 3.3 V ± 10%	4[3]	—	20[3]	mA/V
				V_{DD} = 5.0 V ± 10%	4[3]	—	20[3]	
V_{FXOSC}	CC	T	Oscillation amplitude at EXTAL	f_{OSC} = 40 MHz For both V_{DD} = 3.3 V ± 10%, V_{DD} = 5.0 V ± 10%	—	0.95	—	V
$V_{FXOSCOP}$	CC	P	Oscillation operating point	—	—	1.8		V
I_{FXOSC},[4]	CC	T	Fast external crystal oscillator consumption	V_{DD} = 3.3 V ± 10%, f_{OSC} = 40 MHz	—	2	2.2	mA
				V_{DD} = 5.0 V ± 10%, f_{OSC} = 40 MHz	—	2.3	2.5	
				V_{DD} = 3.3 V ± 10%, f_{OSC} = 16 MHz	—	1.3	1.5	
				V_{DD} = 5.0 V ± 10%, f_{OSC} = 16 MHz	—	1.6	1.8	
$T_{FXOSCSU}$	CC	T	Fast external crystal oscillator start-up time	f_{OSC} = 40 MHz For both V_{DD} = 3.3 V ± 10%, V_{DD} = 5.0 V ± 10%	—	—	5	ms

The transmit outputs (TXD[3:0], TX_EN, TX_ER) can be programmed to transition from either the rising or falling edge of TX_CLK, and the timing is the same in either case. This options allows the use of non-compliant MII PHYs.

Refer to the Fast Ethernet Controller (FEC) chapter of the MPC5646C Reference Manual for details of this option and how to enable it.

Table 45. MII transmit signal timing[1]

Spec	Characteristic	Min	Max	Unit
M5	TX_CLK to TXD[3:0], TX_EN, TX_ER invalid	5	—	ns
M6	TX_CLK to TXD[3:0], TX_EN, TX_ER valid	—	25	ns
M7	TX_CLK pulse width high	35%	65%	TX_CLK period
M8	TX_CLK pulse width low	35%	65%	TX_CLK period

NOTES:
1 Output pads configured with SRE = 0b11.

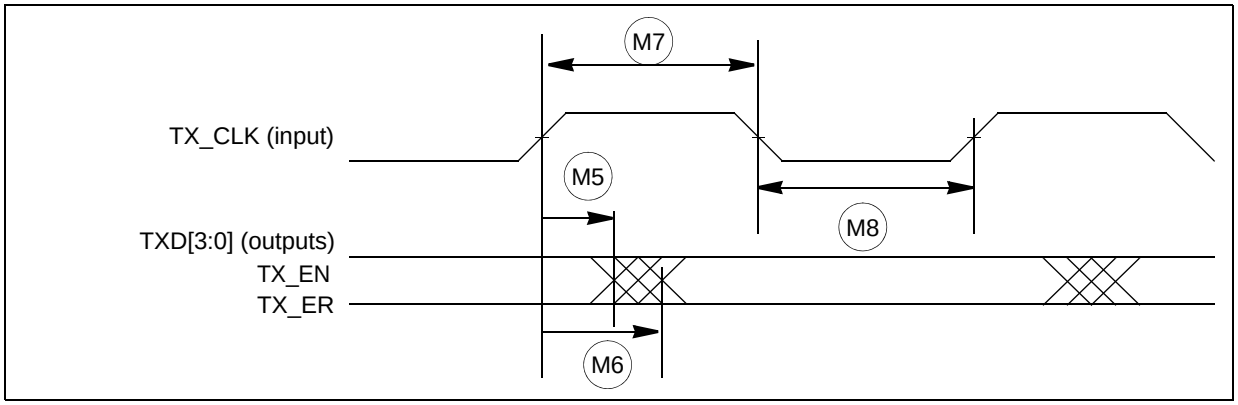


Figure 22. MII transmit signal timing diagram

4.18.3 MII Async Inputs Signal Timing (CRS and COL)

Table 46. MII Async Inputs Signal Timing[1]

Spec	Characteristic	Min	Max	Unit
M9	CRS, COL minimum pulse width	1.5	—	TX_CLK period

NOTES:
1 Output pads configured with SRE = 0b11.

4.19 On-chip peripherals

4.19.1 Current consumption

Table 48. On-chip peripherals current consumption[1]

Symbol		C	Parameter	Conditions		Value[2] Typ	Unit
$I_{DD\_HV\_A(CAN)}$	CC	D	CAN (FlexCAN) supply current on $V_{DD\_HV\_A}$	500 Kbps	Total (static + dynamic) consumption: FlexCAN in loop-back mode XTAL@8 MHz used as CAN engine clock source Message sending period is 580 µs	$7.652 \times f_{periph} + 84.73$	µA
				125 Kbps		$8.0743 \times f_{periph} + 26.757$	
$I_{DD\_HV\_A(eMIOS)}$	CC	D	eMIOS supply current on $V_{DD\_HV\_A}$	Static consumption: eMIOS channel OFF Global prescaler enabled		$28.7 \times f_{periph}$	
				Dynamic consumption: It does not change varying the frequency (0.003 mA)		3	
$I_{DD\_HV\_A(SCI)}$	CC	D	SCI (LINFlex) supply current on $V_{DD\_HV\_A}$	Total (static + dynamic) consumption: LIN mode Baudrate: 20 Kbps		$4.7804 \times f_{periph} + 30.946$	
$I_{DD\_HV\_A(SPI)}$	CC	D	SPI (DSPI) supply current on $V_{DD\_HV\_A}$	Ballast static consumption (only clocked)		1	
				Ballast dynamic consumption (continuous communication): Baudrate: 2 Mbit Transmission every 8 µs Frame: 16 bits		$16.3 \times f_{periph}$	
$I_{DD\_HV\_A(ADC)}$	CC	D	ADC supply current on $V_{DD\_HV\_A}$	V_{DD} = 5.5 V	Ballast static consumption (no conversion)	$0.0409 \times f_{periph}$	mA
				V_{DD} = 5.5 V	Ballast dynamic consumption (continuous conversion)	$0.0049 \times f_{periph}$	
IDD_HV_ADC0	CC	D	ADC_0 supply current on $V_{DD\_HV\_ADC0}$	V_{DD} = 5.5 V	Analog static consumption (no conversion)	200	µA
					Analog dynamic consumption (continuous conversion)	4	mA

Table 48. On-chip peripherals current consumption[1]

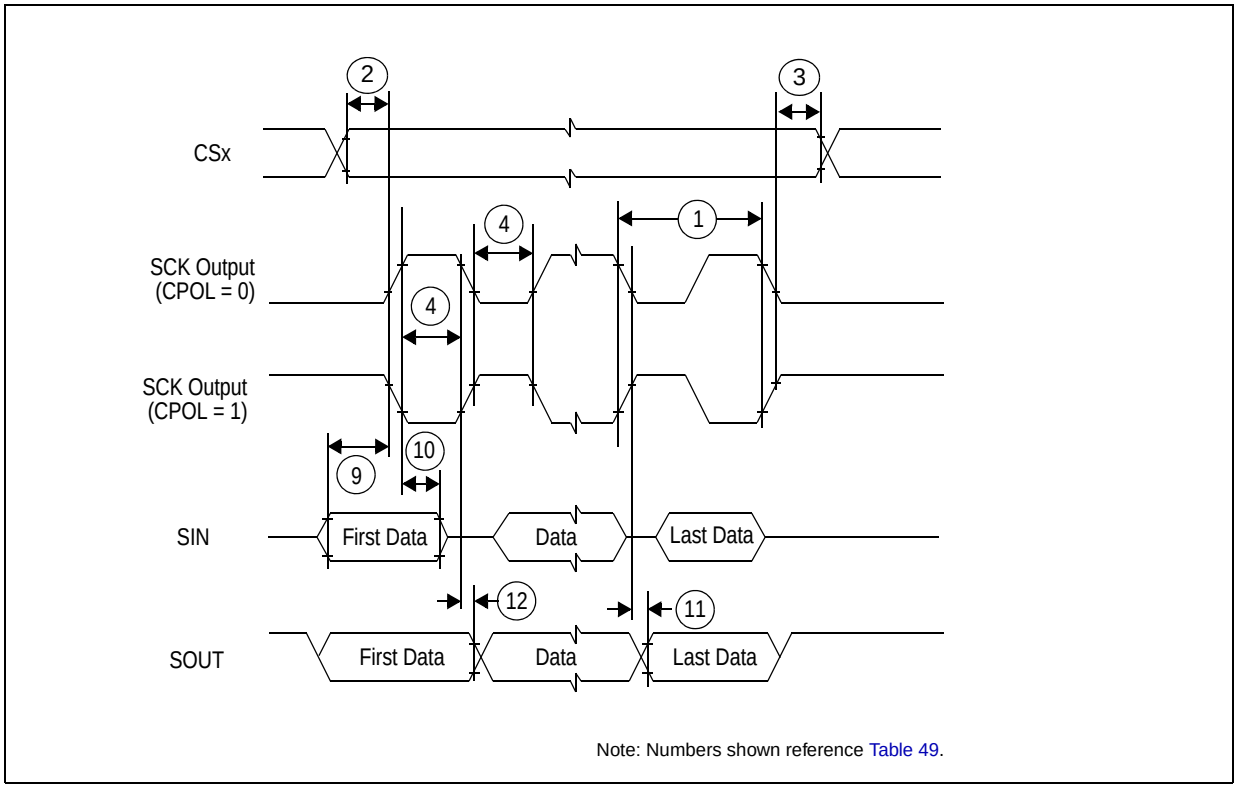
Symbol		C	Parameter	Conditions		Value[2]	Unit
						Typ	
IDD_HV_ADC1	CC	D	ADC_1 supply current on $V_{DD\_HV\_ADC1}$	V_{DD} = 5.5 V	Analog static consumption (no conversion)	300 × f_{periph}	µA
				V_{DD} = 5.5 V	Analog dynamic consumption (continuous conversion)	6	mA
$I_{DD\_HV(FLASH)}$	CC	D	CFlash + DFlash supply current on $V_{DD\_HV\_ADC}$	V_{DD} = 5.5 V	—	13.25	mA
$I_{DD\_HV(PLL)}$	CC	D	PLL supply current on V_{DD_HV}	V_{DD} = 5.5 V	—	0.0031 × f_{periph}	

NOTES:
1 Operating conditions: T_A = 25 °C, f_{periph} = 8 MHz to 120 MHz.
2 f_{periph} is in absolute value.

4.19.2 DSPI characteristics

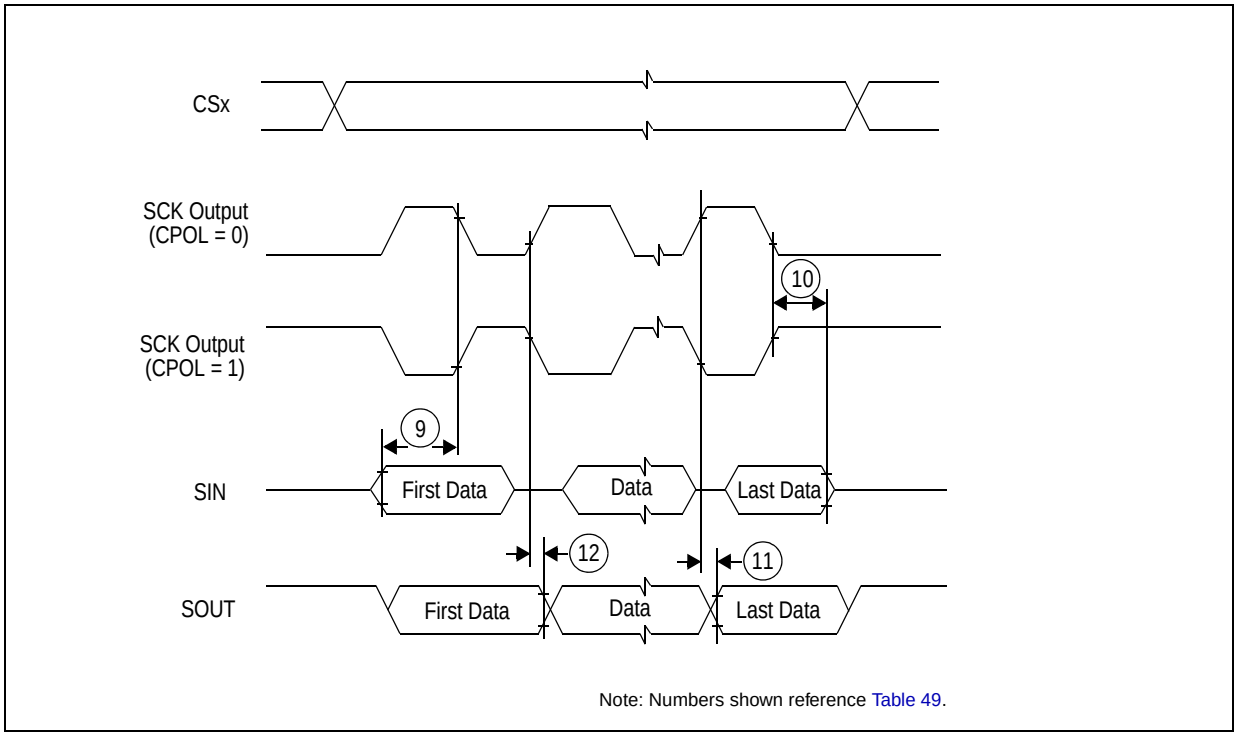
Table 49. DSPI timing

Spec	Characteristic	Symbol	Min	Max	Unit
1	DSPI Cycle Time	t_{SCK}	Refer note[1]	—	ns
—	Internal delay between pad associated to SCK and pad associated to CSn in master mode for CSn1->0	Δt_{CSC}	—	115	ns
—	Internal delay between pad associated to SCK and pad associated to CSn in master mode for CSn1->1	Δt_{ASC}	15	—	ns
2	CS to SCK Delay[2]	t_{CSC}	7	—	ns
3	After SCK Delay[3]	t_{ASC}	15	—	ns
4	SCK Duty Cycle	t_{SDC}	$0.4 \times t_{SCK}$	$0.6 \times t_{SCK}$	ns
—	Slave Setup Time ($\overline{SS}$ active to SCK setup time)	t_{SUSS}	5	—	ns
—	Slave Hold Time ($\overline{SS}$ active to SCK hold time)	t_{HSS}	10	—	ns
5	Slave Access Time ($\overline{SS}$ active to SOUT valid)[4]	t_A	—	42	ns
6	Slave SOUT Disable Time ($\overline{SS}$ inactive to SOUT High-Z or invalid)	t_{DIS}	—	25	ns
7	CSx to $\overline{PCSS}$ time	t_{PCSC}	0	—	ns
8	$\overline{PCSS}$ to PCSx time	t_{PASC}	0	—	ns



Note: Numbers shown reference Table 49.

Figure 25. DSPI classic SPI timing–master, CPHA = 0



Note: Numbers shown reference Table 49.

Figure 26. DSPI classic SPI timing–master, CPHA = 1

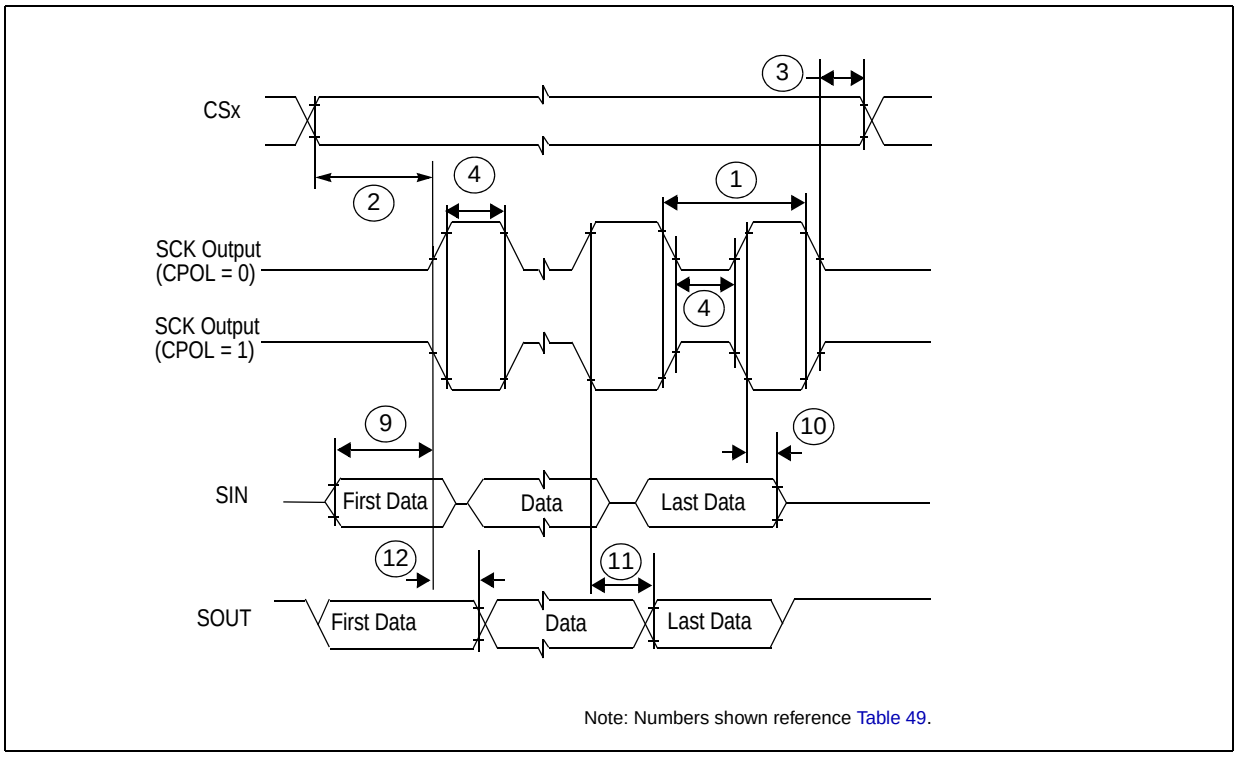


Figure 29. DSPI modified transfer format timing–master, CPHA = 0

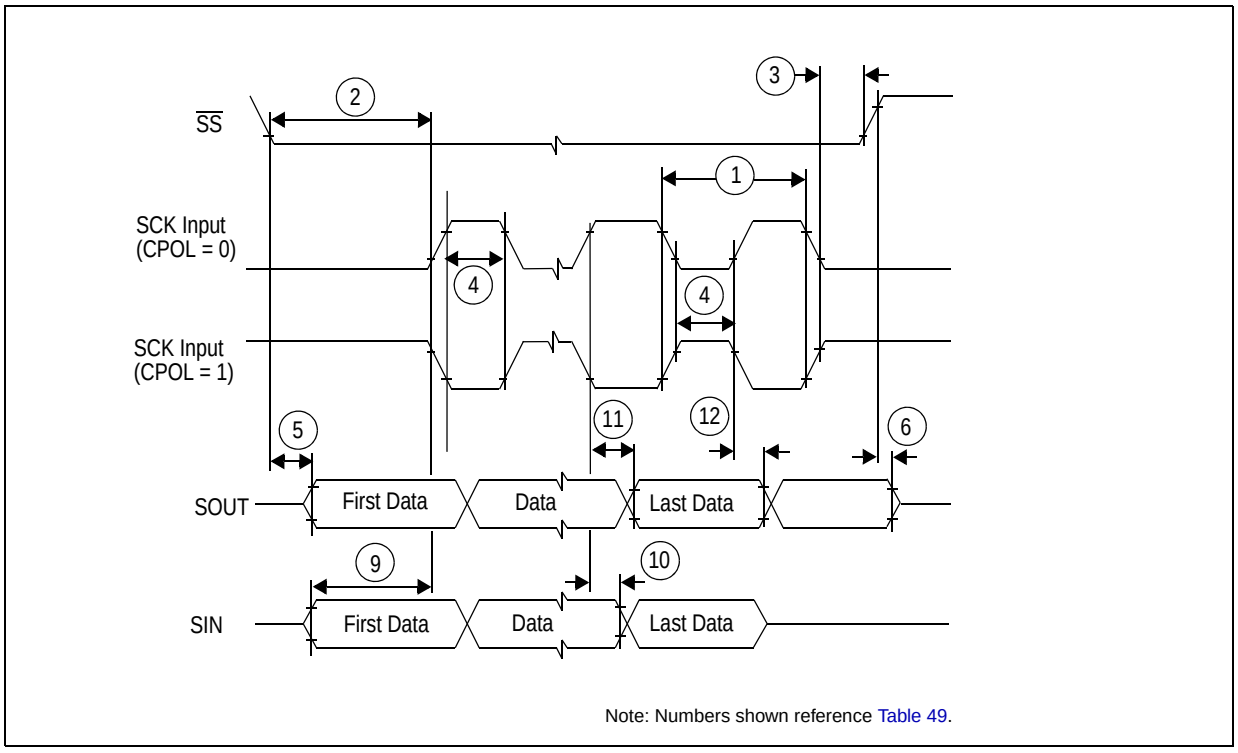


Figure 31. DSPI modified transfer format timing–slave, CPHA = 0

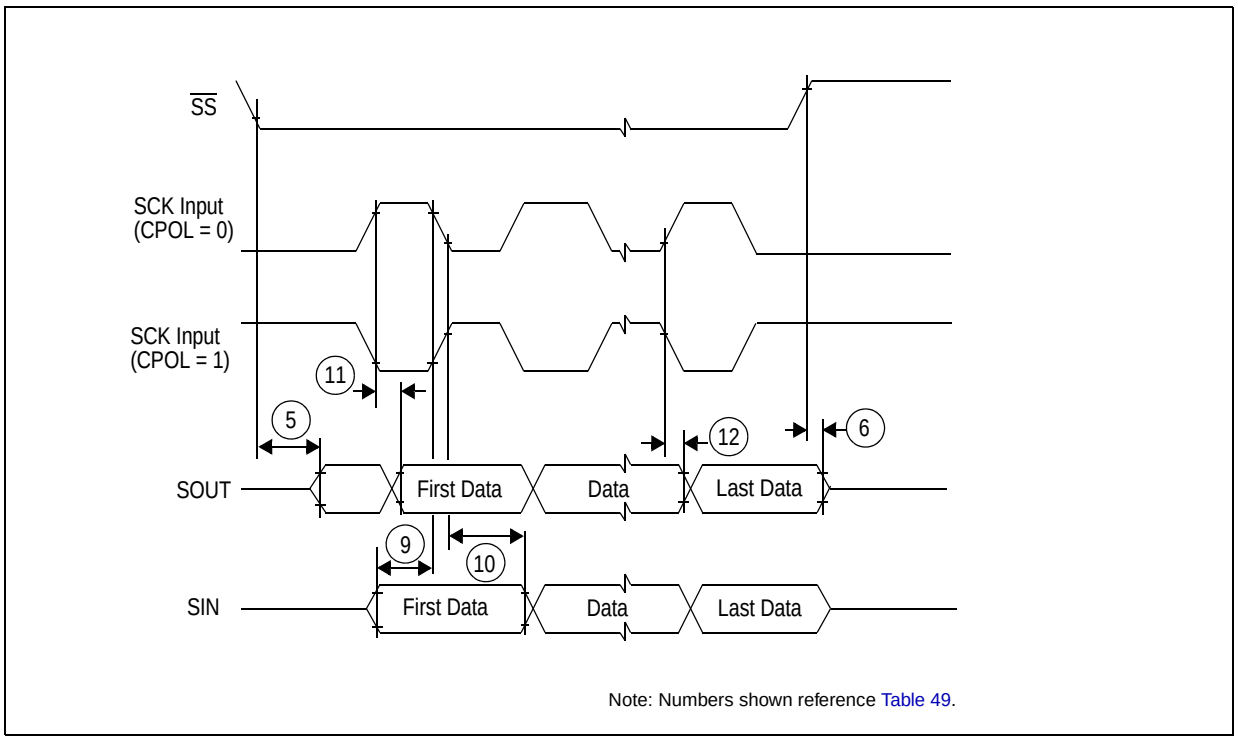


Figure 32. DSPI modified transfer format timing–slave, CPHA = 1

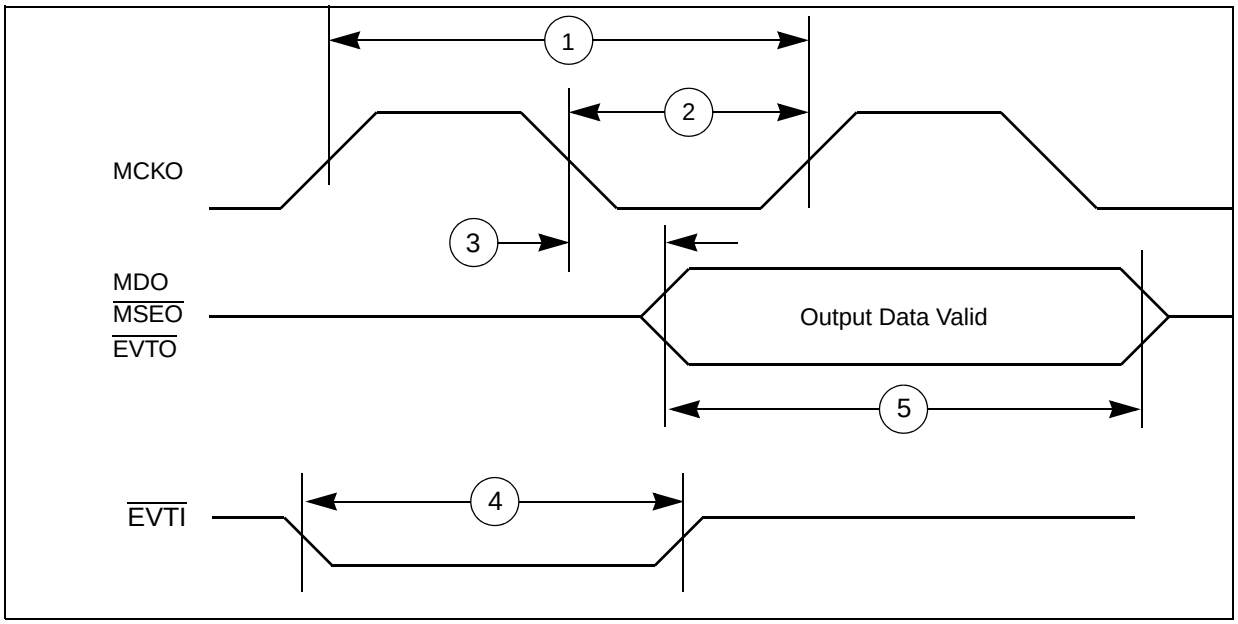


Figure 34. Nexus output timing

5 Package characteristics

5.1 Package mechanical data

5.1.1 176 LQFP package mechanical drawing

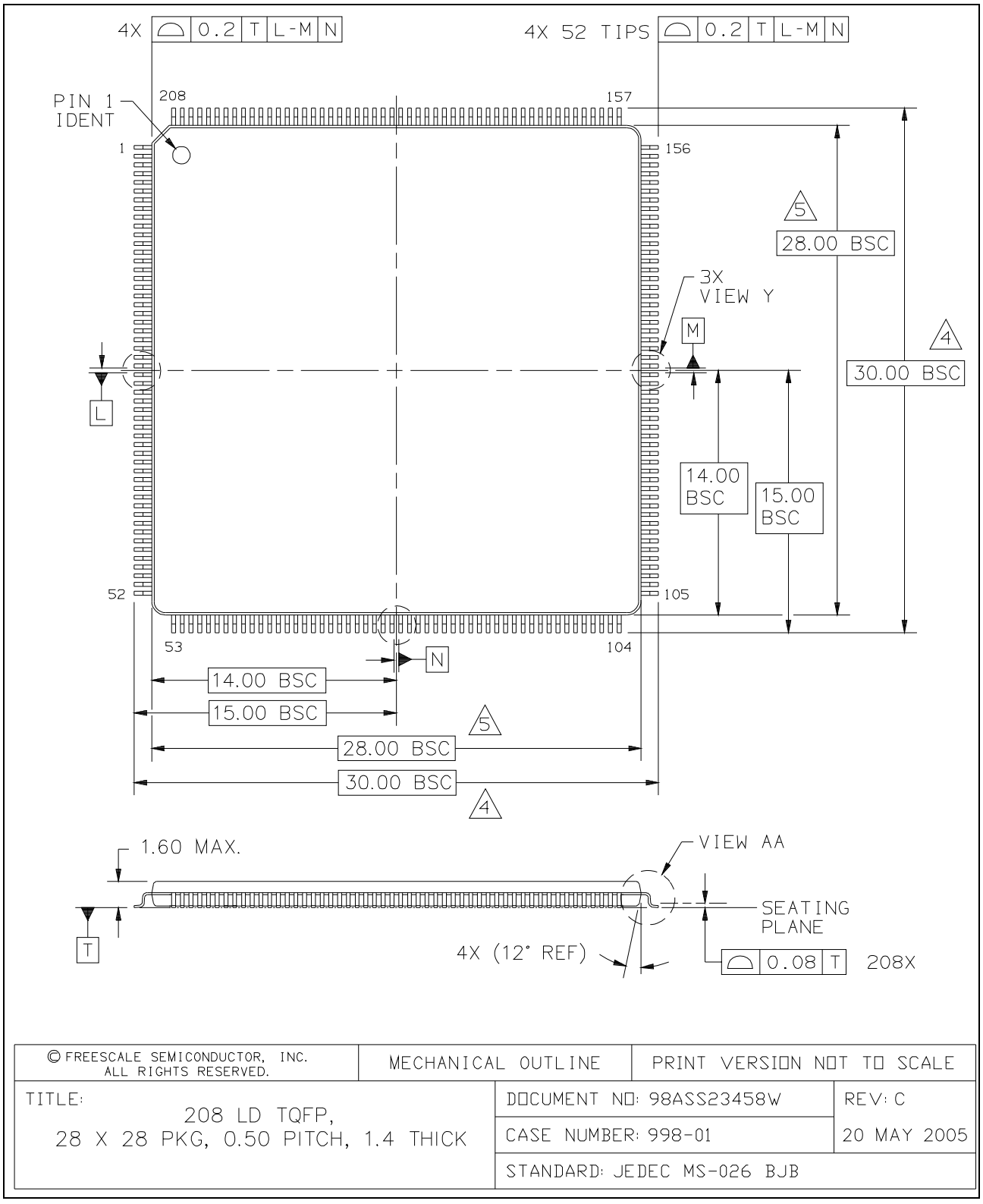


Figure 40. 208 LQFP mechanical drawing (Part 1 of 3)

7 Revision history

Table 52 summarizes revisions to this document.

Table 52. Revision history

Revision	Date	Changes
1	15 April 2010	Initial Release
2	17 August 2010	• Editing and formatting updates throughout the document. • Updated Voltage regulator capacitance connection figure. • Added a new sub-section "V_{DD_BV} Options" • Program and erase specifications: -Updated Tdwprogram TYP to 22 us -Updated T128Kpperase Max to 5000 ms -Added t_{ESUS} parameter • Added 208 MAPBGA thermal characteristics • Added recommendation in the Voltage regulator electrical characteristics section. • Added Crystal description table in Fast external crystal oscillator (4 to 140 MHz) electrical characteristics section and corrected the cross-reference to the same. • Added new sections - Pad types, System pins and functional ports • Updated TYP numbers in the Flash program and erase specifications table • Added a new table: Program and erase specifications (Data Flash) • Flash read access timing table: Added Data flash memory numbers • Flash power supply DC electrical characteristics table: Updated IDFREAD and IDFMOD values for Data flash, Removed IDFLPW parameter • Updated feature list. • MPC5646C 3M family comparison table: Updated ADC channels and added ADC footnotes. • MPC5646C 3M block diagram: Updated ADC channels and added legends. • MPC5646C 3M series block summary: Added new blocks. • Functional Port Pin Descriptions table: Added OSC32k_XTAL and OSC32k_EXTAL function at PB8 and PB9 port pins. • Electrical Characteristics: Replaced VSS with VSS_HV throughout the section. • Absolute maximum ratings, Recommended operating conditions (3.3 V) and Recommended operating conditions (5.0 V) tables: VRC_CTRL min is updated to "0". • Recommended operating conditions (3.3 V) and Recommended operating conditions (5.0 V) tables: Clarified VIN parameter, clarified footnote 2 in both tables. • LQFP thermal characteristics section: Updated numbers for LQFP packages. • Low voltage power domain electrical characteristics table: Clarified footnotes based upon review comments. • Code flash memory—Program and erase specifications: Updated tESRT to 20 ms. • ADC electrical characteristics section: Replace ADC0 with ADC_0 and ADC1 with ADC_1 throughout the document. • DSPI characteristics section: Replaced PCSx with CSx in all figures and tables.